

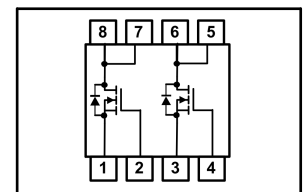
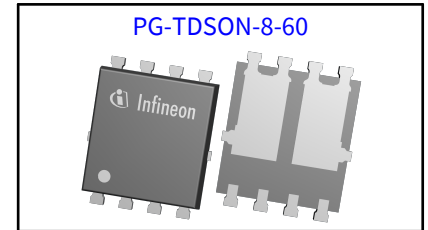
Automotive MOSFET

OptiMOS™ 5 Power-Transistor



Features

- OptiMOS™ power MOSFET for automotive applications
- N-channel – Enhancement mode – Logic Level
- Extended qualification beyond AEC-Q101
- Enhanced electrical testing
- Robust design
- MSL1 up to 260°C peak reflow
- 175°C operating temperature
- RoHS compliant
- 100% Avalanche tested



Potential Applications

General automotive applications.

Product Validation

Qualified for automotive applications. Product validation according to AEC-Q101.

Product Summary

V_{DS}	100	V
$R_{DS(on)}$	9.40	mΩ
I_D (chip limited)	66	A

Type	Package	Marking
IAUCN10S5L094D	PG-TDSON-8-60	5N1L094D

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Maximum Ratings

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	$V_{GS} = 10\text{ V}$, Chip limitation ^{1,2)}	66	A
		$V_{GS} = 10\text{ V}$, DC current	60	
		$T_a = 85^\circ\text{C}$, $V_{GS} = 10\text{ V}$, R_{thJA} on 2s2p ^{2,3)}	10	
Pulsed drain current ²⁾	$I_{D,pulse}$	$T_C = 25^\circ\text{C}$, $t_p = 100\ \mu\text{s}$	170	
Avalanche energy, single pulse ²⁾	E_{AS}	$I_D = 28\text{ A}$	38	mJ
Avalanche current, single pulse	I_{AS}	–	28	A
Gate source voltage	V_{GS}	–	± 20	V
Power dissipation	P_{tot}	$T_C = 25^\circ\text{C}$	94	W
Operating and storage temperature	T_j, T_{stg}	–	-55 ... +175	$^\circ\text{C}$

Thermal Characteristics²⁾

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal resistance, junction - case	R_{thJC}	–	–	–	1.6	K/W
Thermal resistance, junction - ambient ³⁾	R_{thJA}	–	–	40	–	

Electrical Characteristics

 at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Static Characteristics

Drain-source breakdown voltage	$V_{(Br)DSS}$	$V_{GS} = 0\text{ V}$, $I_D = 1\text{ mA}$	100	–	–	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 35\text{ }\mu\text{A}$	1.2	1.7	2.2	
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 100\text{ V}$, $V_{GS} = 0\text{ V}$, $T_j = 25\text{ °C}$	–	–	1	μA
		$V_{DS} = 100\text{ V}$, $V_{GS} = 0\text{ V}$, $T_j = 100\text{ °C}^{2)}$	–	–	100	
Gate-source leakage current	I_{GSS}	$V_{GS} = 20\text{ V}$, $V_{DS} = 0\text{ V}$	–	–	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 4.5\text{ V}$, $I_D = 30\text{ A}$	–	10.80	14.60	m Ω
		$V_{GS} = 10\text{ V}$, $I_D = 30\text{ A}$	–	8.30	9.40	
Gate resistance ²⁾	R_G	–	–	1.1	–	Ω

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Dynamic Characteristics²⁾						
Input capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 50\text{ V}, f = 1\text{ MHz}$	-	1611	2094	pF
Output capacitance	C_{oss}		-	273	355	
Reverse transfer capacitance	C_{rss}		-	14	21	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 50\text{ V}, V_{GS} = 10\text{ V}, I_D = 30\text{ A}, R_G = 3.5\ \Omega$	-	5	-	ns
Rise time	t_r		-	3	-	
Turn-off delay time	$t_{d(off)}$		-	16	-	
Fall time	t_f		-	7	-	

Gate Charge Characteristics²⁾

Gate to source charge	Q_{gs}	$V_{DD} = 50\text{ V}, I_D = 30\text{ A}, V_{GS} = 0\text{ to }10\text{ V}$	-	5.2	7	nC
Gate to drain charge	Q_{gd}		-	4.3	6	
Gate charge total	Q_g		-	23	30	
Gate plateau voltage	$V_{plateau}$		-	3.2	-	V

Reverse Diode

Diode continuous forward current ²⁾	I_S	$T_C = 25^\circ\text{C}$	-	-	60	A
Diode pulse current ²⁾	$I_{S,pulse}$	$T_C = 25^\circ\text{C}, t_p = 100\ \mu\text{s}$	-	-	170	
Diode forward voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_F = 30\text{ A}, T_j = 25^\circ\text{C}$	-	0.9	1.1	V
Reverse recovery time ²⁾	t_{rr}	$V_R = 50\text{ V}, I_F = 50\text{ A}, di_F/dt = 100\text{ A}/\mu\text{s}$	-	30	-	ns
Reverse recovery charge ²⁾	Q_{rr}		-	20	-	nC

¹⁾ Practically the current is limited by the overall system design including the customer-specific PCB.

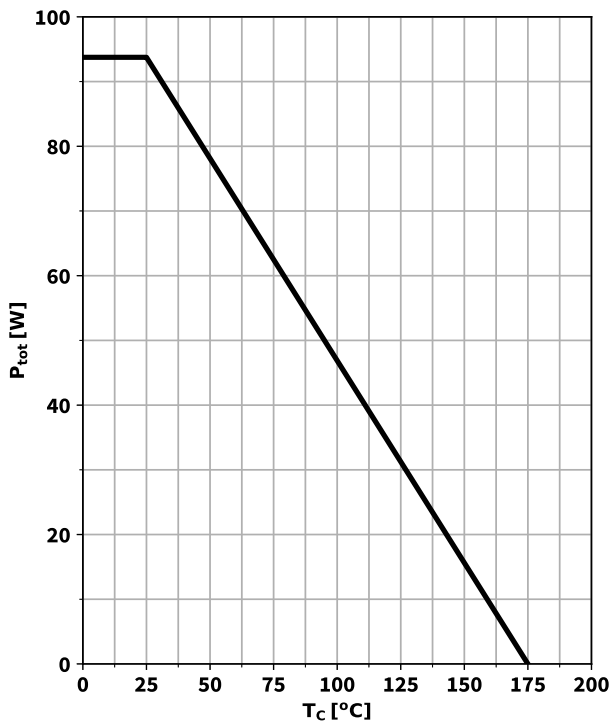
²⁾ The parameter is not subject to production testing – specified by design.

³⁾ Device on 2s2p FR4 PCB defined in accordance with JEDEC standards (JESD51-5, -7). PCB is vertical in still air.

Electrical characteristics diagrams

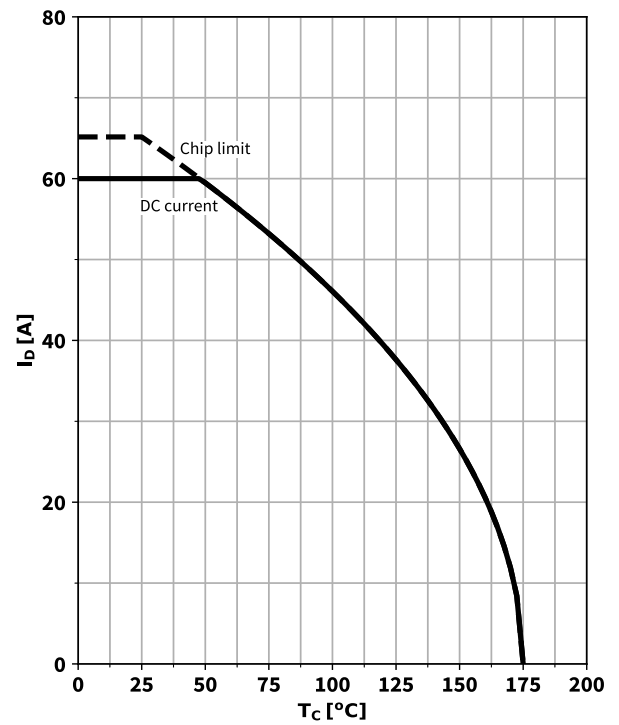
1 Power dissipation

$$P_{tot} = f(T_C); V_{GS} \geq 6 \text{ V}$$



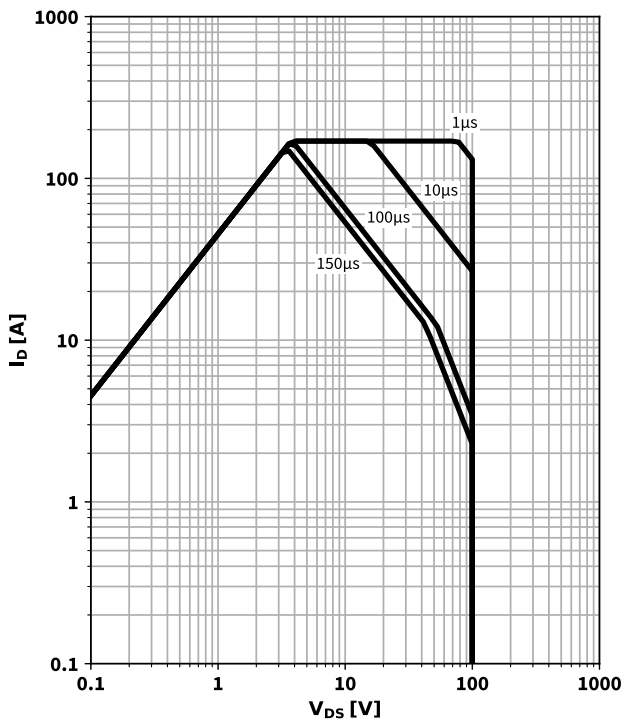
2 Drain current

$$I_D = f(T_C); V_{GS} \geq 6 \text{ V}$$



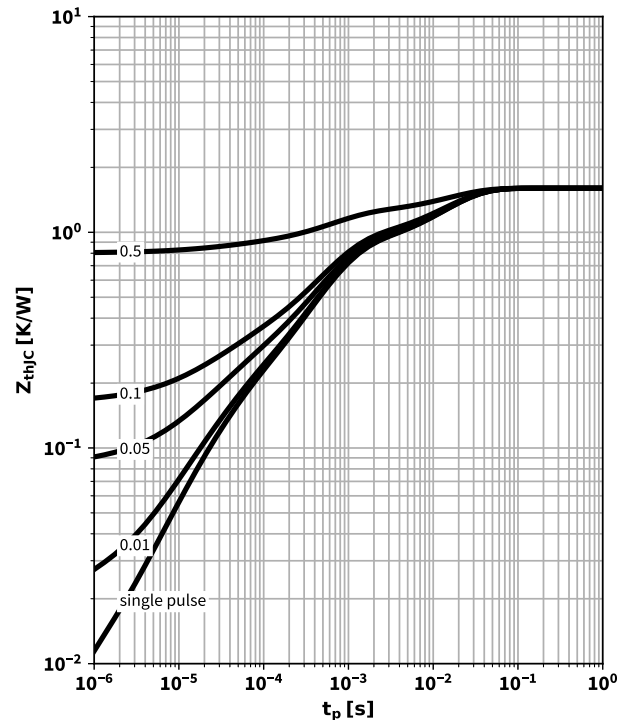
3 Safe operating area

$$I_D = f(V_{DS}); T_C = 25 \text{ °C}; D = 0; \text{ parameter: } t_p$$



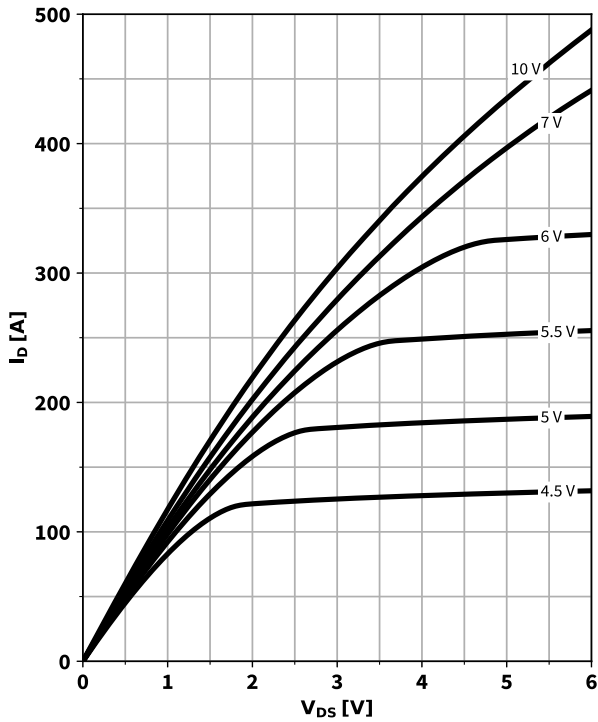
4 Max. transient thermal impedance

$$Z_{thJC} = f(t_p); \text{ parameter: } D = t_p/T$$



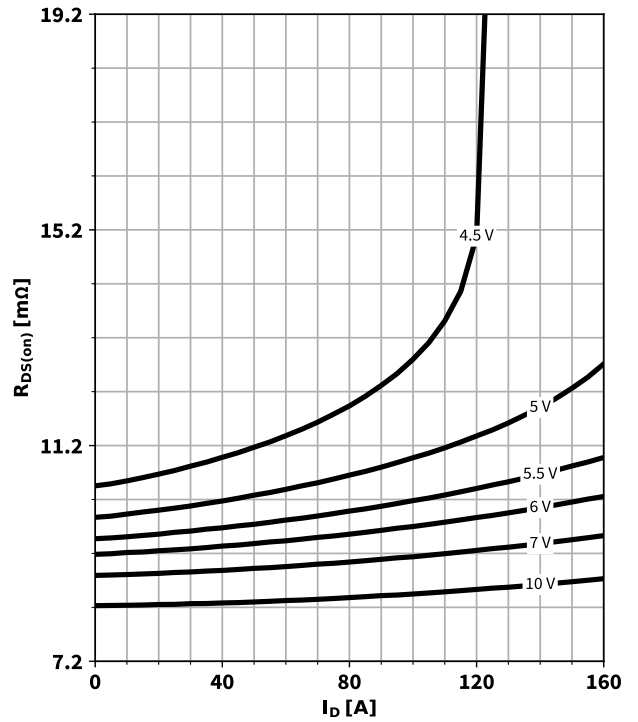
5 Typ. output characteristics

$I_D = f(V_{DS}); T_j = 25^\circ\text{C};$ parameter: V_{GS}



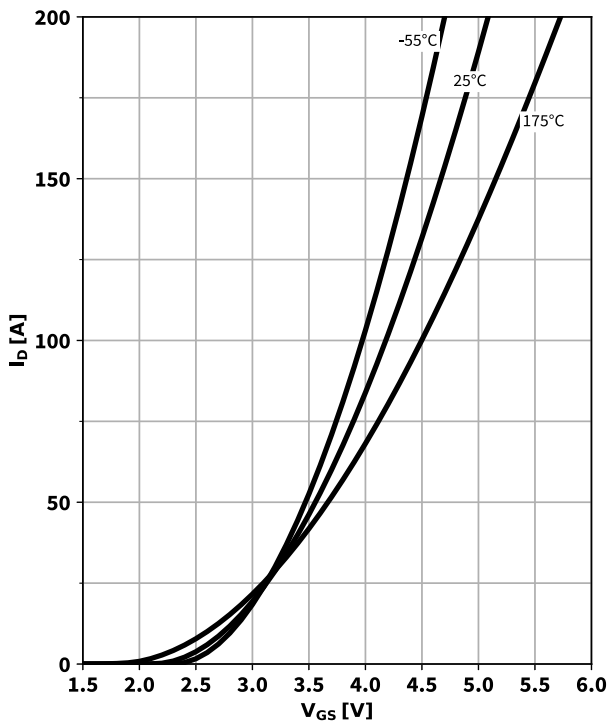
6 Typ. drain-source on-state resistance

$R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C};$ parameter: V_{GS}



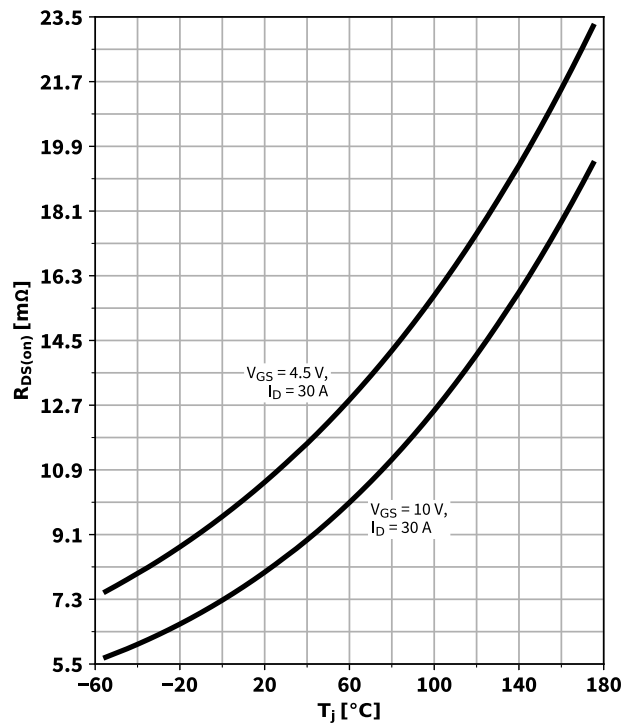
7 Typ. transfer characteristics

$I_D = f(V_{GS}); V_{DS} = 6\text{ V};$ parameter: T_j



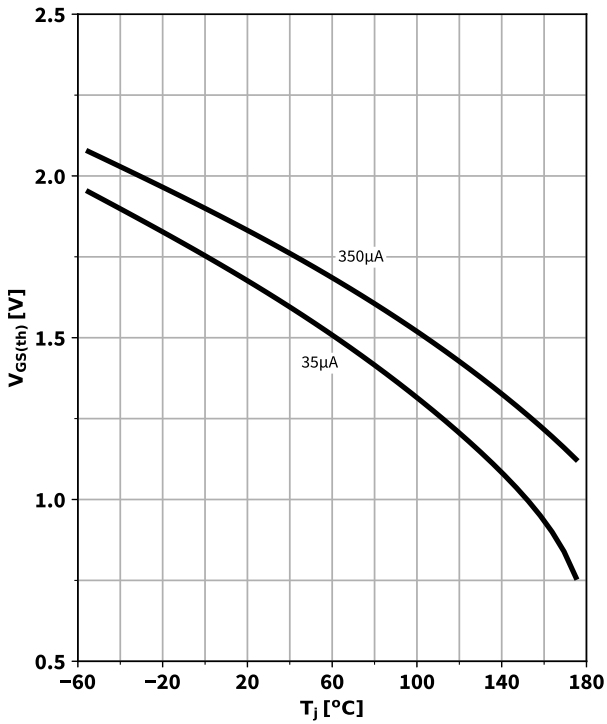
8 Typ. drain-source on-state resistance

$R_{DS(on)} = f(T_j);$ parameter: I_D, V_{GS}



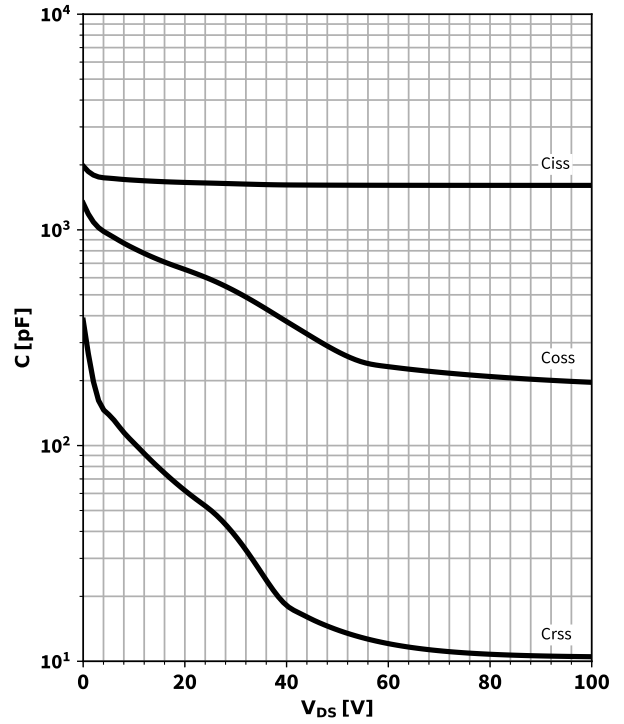
9 Typ. gate threshold voltage

$V_{GS(th)} = f(T_j)$; $V_{GS} = V_{DS}$; parameter: I_D



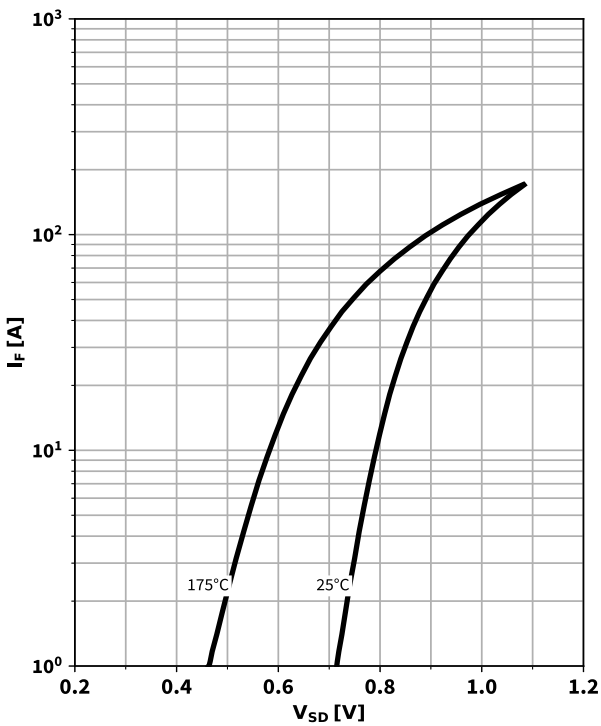
10 Typ. capacitances

$C = f(V_{DS})$; $V_{GS} = 0 V$; $f = 1 MHz$



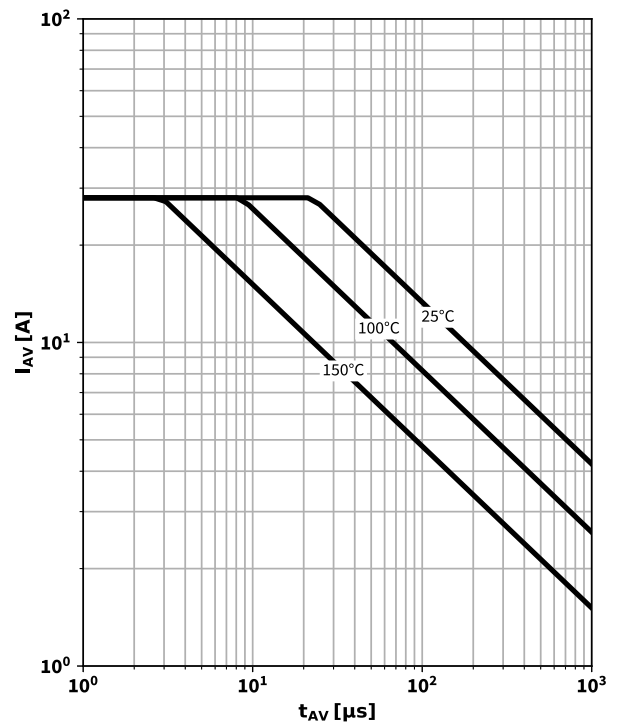
11 Typ. forward diode characteristics

$I_F = f(V_{SD})$; parameter: T_j



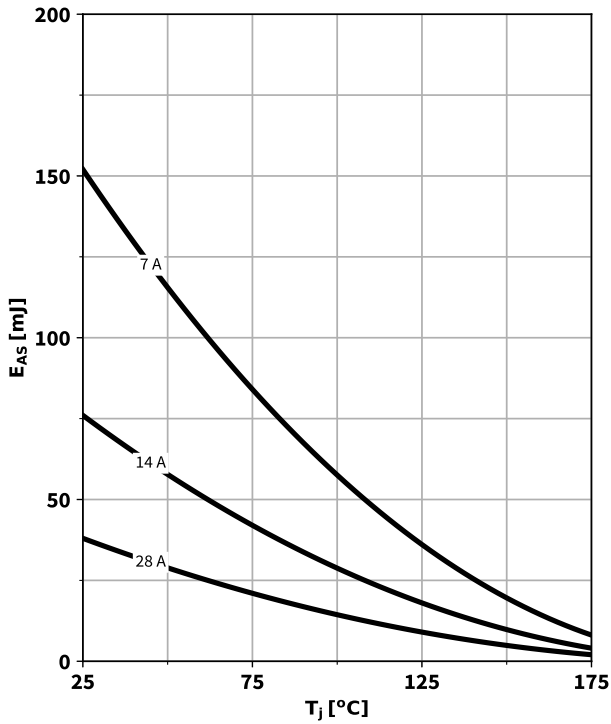
12 Typ. avalanche characteristics

$I_{AS} = f(t_{AV})$; parameter: $T_{j(start)}$



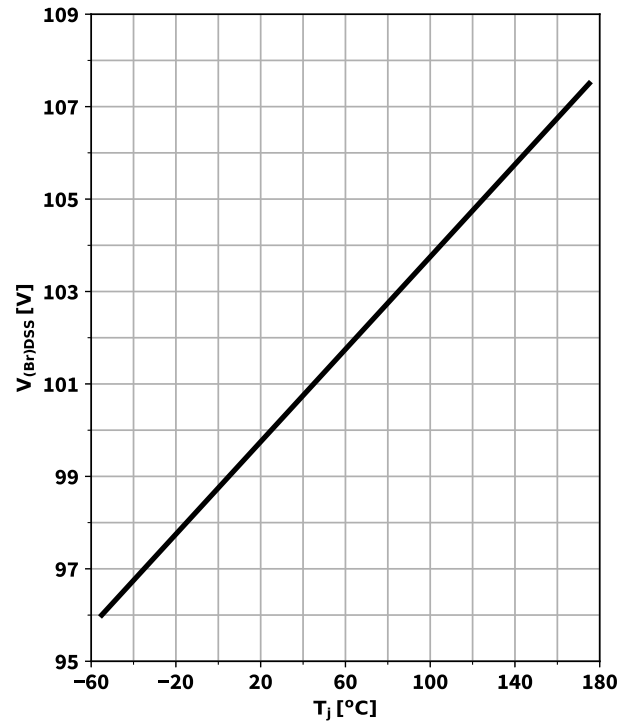
13 Typical avalanche energy

$E_{AS} = f(T_j)$; parameter: I_D



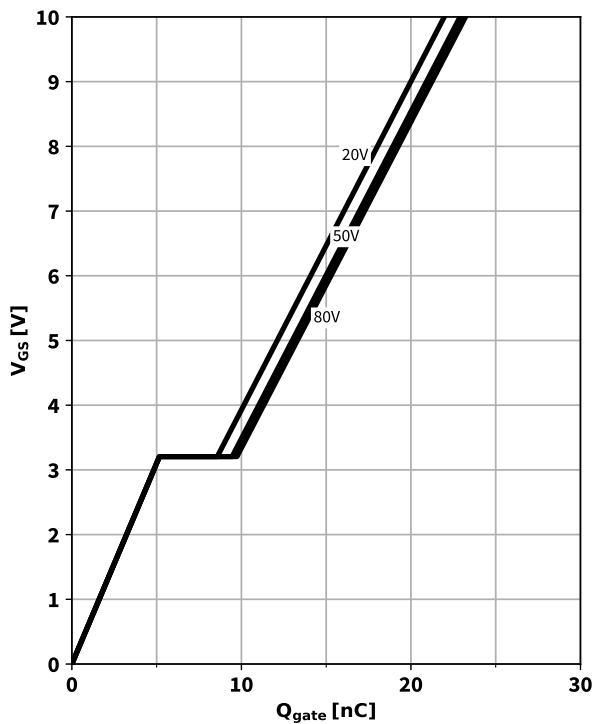
14 Drain-source breakdown voltage

$V_{(BR)DSS} = f(T_j)$; $I_D = 1 \text{ mA}$

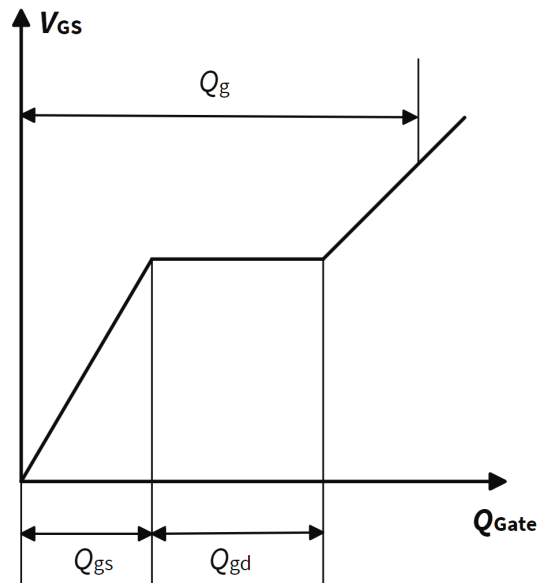


15 Typ. gate charge

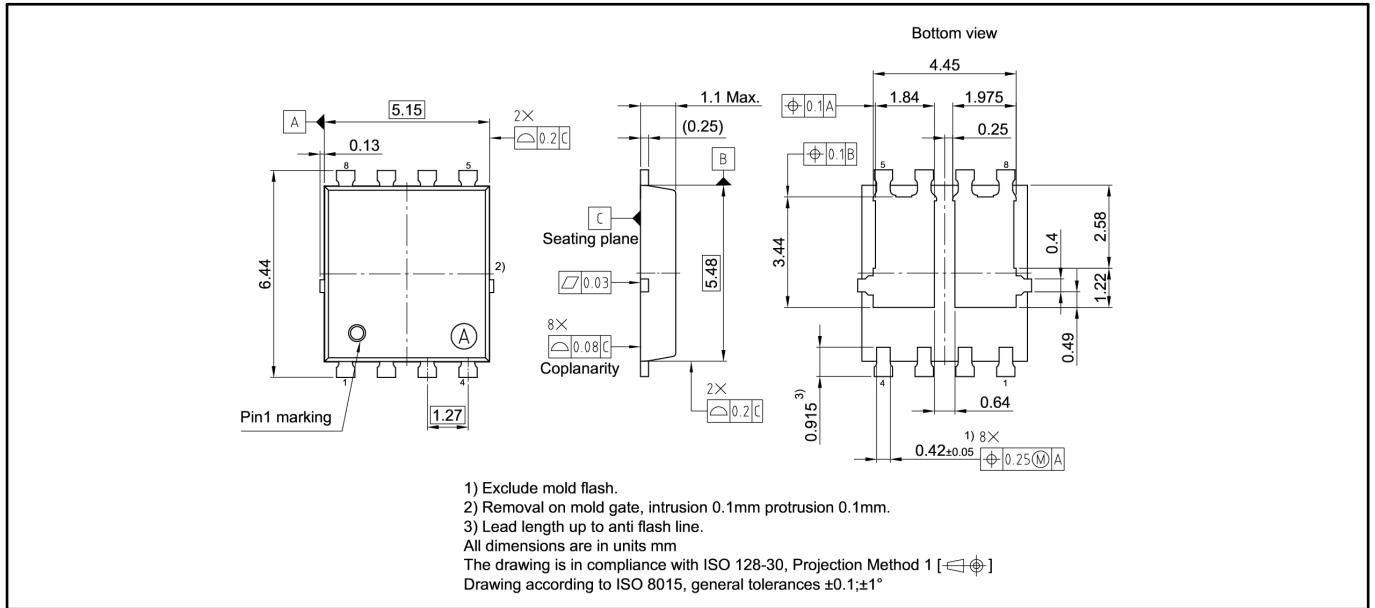
$V_{GS} = f(Q_{gate})$; $I_D = 30 \text{ A}$ pulsed; parameter: V_{DD}



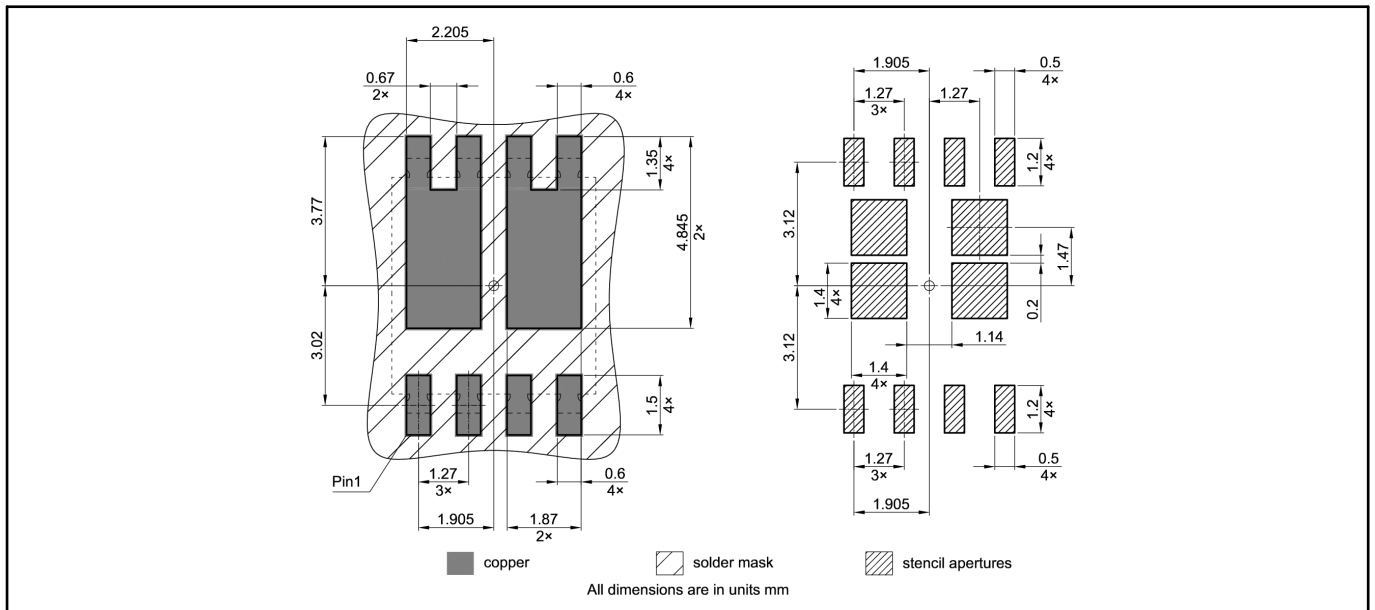
16 Gate charge waveforms



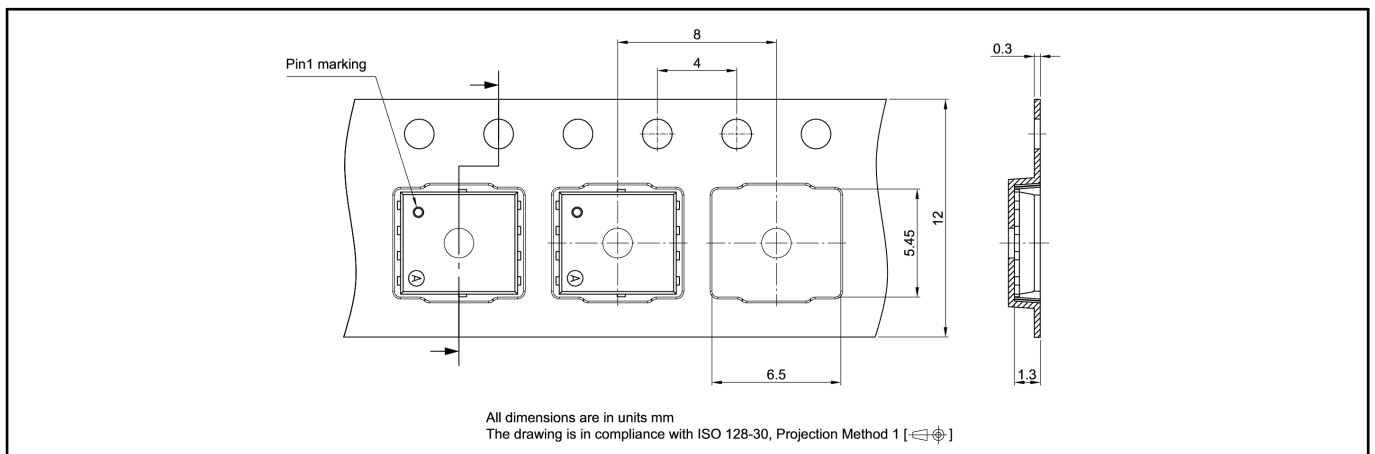
Package Outline



Footprint



Packaging





Revision History

Revision	Date	Changes
Revision 1.0	2024-05-08	Final Data Sheet

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